

2SC1573, 2SC1573A, 2SC1573B

Silicon NPN triple diffusion planar type

For high breakdown voltage general amplification

For small TV video output

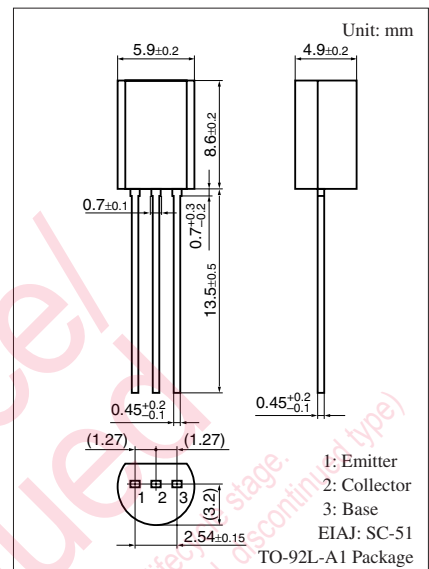
Complementary to 2SC1573 and 2SA0879

■ Features

- High collector-emitter voltage (Base open) V_{CE0}
- High transition frequency f_T

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	2SC1573	V_{CBO}	250	V
	2SC1573A		300	
	2SC1573B		400	
Collector-emitter voltage (Base open)	2SC1573	V_{CEO}	200	V
	2SC1573A		300	
	2SC1573B		400	
Emitter-base voltage (Collector open)	2SC1573	V_{EBO}	5	V
	2SC1573A		7	
	2SC1573B			
Collector current	I_C	70	mA	
Peak collector current	I_{CP}	100	mA	
Collector power dissipation	P_C	1	W	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	



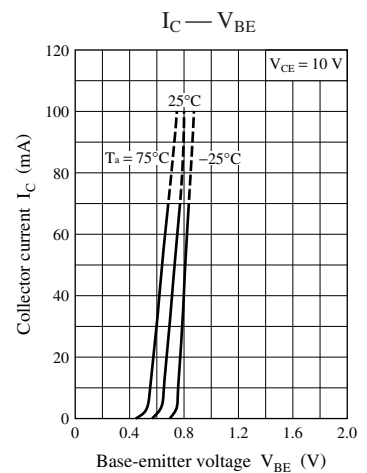
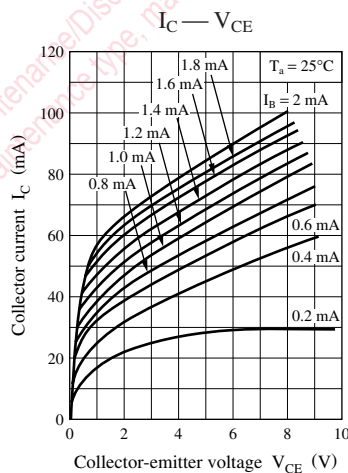
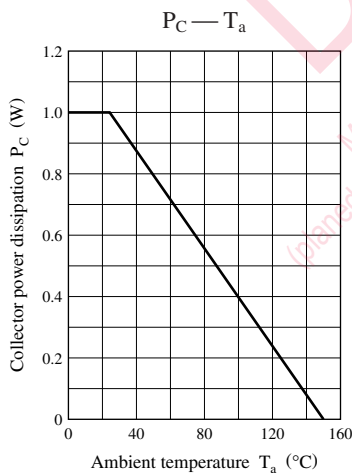
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

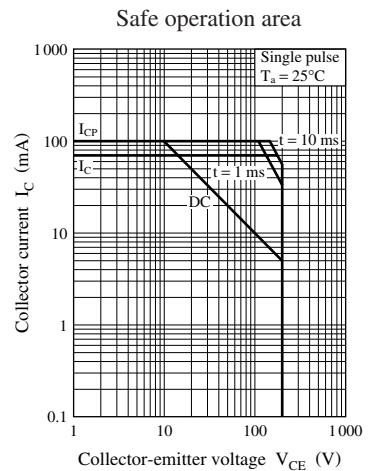
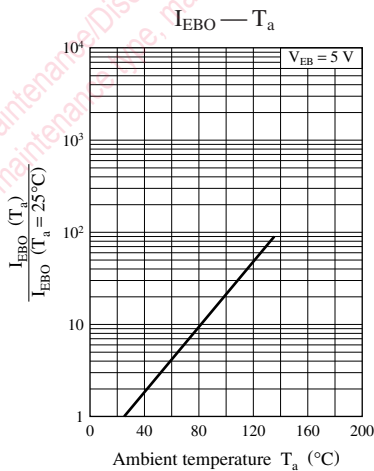
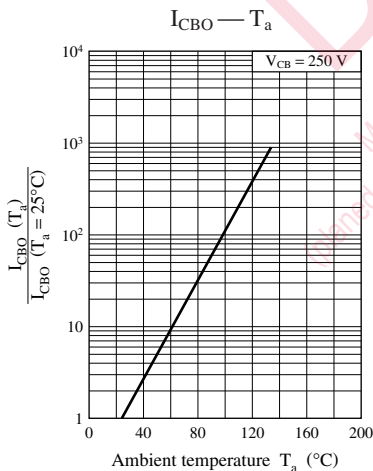
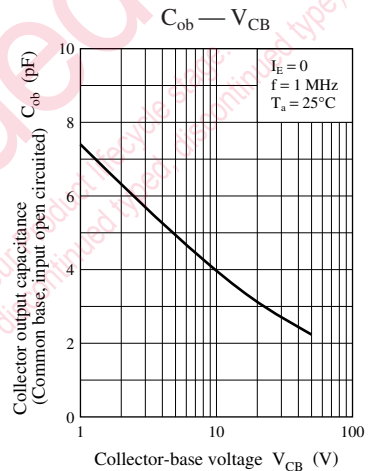
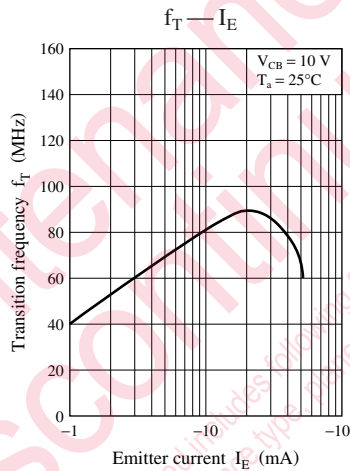
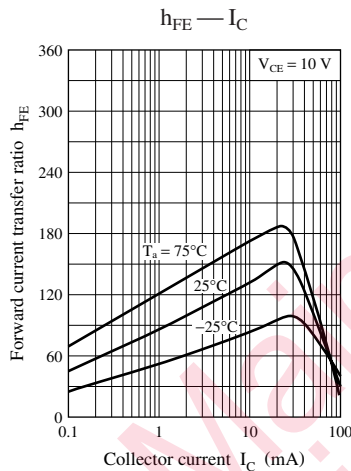
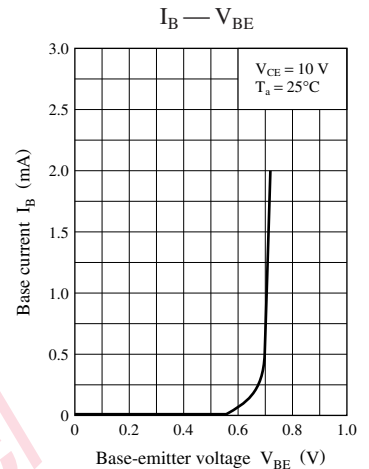
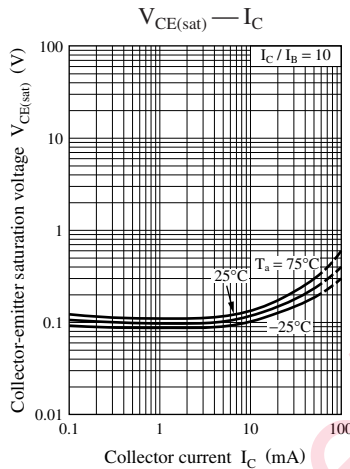
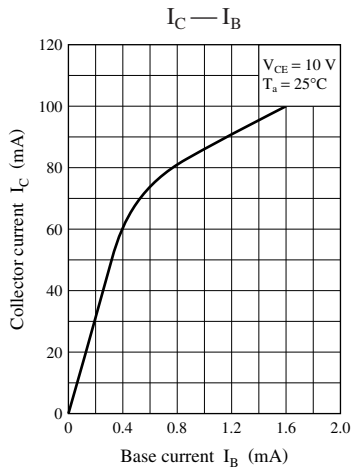
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SC1573	V_{CEO}	$I_C = 100 \mu\text{A}, I_B = 0$	200			V
	2SC1573A			300			
	2SC1573B			400			
Emitter-base voltage (Collector open)	2SC1573	V_{EBO}	$I_E = 1 \mu\text{A}, I_C = 0$	5			V
	2SC1573A			7			
	2SC1573B			7			
Collector-base cut-off current (Emitter open)	2SC1573	I_{CBO}	$V_{CB} = 12 \text{ V}, I_E = 0$			2	μA
	2SC1573A						
	2SC1573B		$V_{CB} = 200 \text{ V}, I_E = 0$			10	
Forward current transfer ratio	2SC1573	h_{FE}^*	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	60		220	—
	2SC1573A			30		220	
	2SC1573B						
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.2	V
Transition frequency		f_T	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$	50	80		MHz
Collector output capacitance (Common base, input open circuited)	2SC1573	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		5	10	pF
	2SC1573A				4	8	
	2SC1573B				4	8	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification (2SC1573 for ranks Q and R only)

Rank	P	Q	R
h_{FE}	30 to 100	60 to 150	100 to 220





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